Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 17 A, 190 m Ω

Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

Features

- 700 V @ T_I= 150°C
- Typ. $R_{DS(on)} = 159 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 33 \text{ nC}$)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 300 pF)
- 100% Avalanche Tested
- This Device is Pb-Free and is RoHS Compliant

Applications

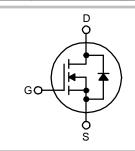
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



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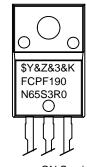
V _{DSS}	R _{DS(on)} MAX	I _D MAX
650 V	190 mΩ @ 10 V	17 A





TO-220 CASE 340BF

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code

kK = Lot Code

FCPF190N65S3R0 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter		FCPF190N65S3R0L	Unit	
V_{DSS}	Drain to Source Voltage		650	V	
V_{GSS}	Gate to Source Voltage	DC	±30	V	
		AC (f > 1 Hz)	±30	V	
I _D	Drain Current	Continuous (T _C = 25°C)	17*	А	
		Continuous (T _C = 100°C)	11*	1	
I _{DM}	Drain Current	Pulsed (Note 1)	42.5*	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		76	mJ	
I _{AS}	Avalanche Current (Note 2)		2.5	А	
E _{AR}	Repetitive Avalanche Energy (Note 1)		1.44	mJ	
dv/dt	MOSFET dv/dt		100	V/ns	
	Peak Diode Recovery dv/dt	Peak Diode Recovery dv/dt (Note 3)		1	
P_{D}	Power Dissipation	T _C = 25°C	33	W	
		Derate Above 25°C	1.15	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		−55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality stresses exceeding those listed in the Maximum Ratings table may damage it should not be assumed, damage may occur and reliability may be affected. *Drain current limited by maximum junction temperature.
1. Repetitive rating: pulse–width limited by maximum junction temperature.
2. $I_{AS} = 2.5 \text{ A}$, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}\text{C}$.
3. $I_{SD} \le 8.5 \text{ A}$, di/dt $\le 200 \text{ A/ms}$, $V_{DD} \le 400 \text{ V}$, starting $T_J = 25^{\circ}\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	FCPF190N65S3R0L	Unit
Rejc	Thermal Resistance, Junction to Case, Max.	3.76	°C/W
Reja	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF190N65S3R0L	FCPF190N65S3R0	TO-220F	Tube	N/A	N/A	50 Units

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
OFF CHARACT	ERISTICS					
BV _{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^{\circ}\text{C}$	650	_	-	V
		$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 150^{\circ}\text{C}$	700	-	-	V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.6	_	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	-	-	1	μΑ
		V _{DS} = 520 V, T _C = 125°C	-	0.89	-	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA
ON CHARACTE	RISTICS					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 1.7 \text{ mA}$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$	-	159	190	mΩ
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 8.5 \text{ A}$	-	10	-	S
YNAMIC CHA	RACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V},$	-	1350	_	pF
C _{oss}	Output Capacitance	f = 1 MHz	-	30	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	300	-	pF
C _{oss(er.)}	Energy Related Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	43	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	$V_{DS} = 400 \text{ V}, I_{D} = 8.5 \text{ A},$	-	33	-	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V (Note 4)	-	7.9	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	(,	-	14	_	nC
ESR	Equivalent Series Resistance	f = 1 MHz	_	0.5	_	Ω
WITCHING CH	HARACTERISTICS				I	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 400 \text{ V}, I_D = 8.5 \text{ A},$	_	17	_	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V, } R_g = 4.7 \Omega$ (Note 4)	-	16	_	ns
t _{d(off)}	Turn-Off Delay Time		-	42	-	ns
t _f	Turn-Off Fall Time		-	6	-	ns
SOURCE-DRA	IN DIODE CHARACTERISTICS				•	
IS	Maximum Continuous Source to Dra	ain Diode Forward Current	-	_	17	Α
I _{SM}	Maximum Pulsed Source to Drain	Diode Forward Current	-	-	42.5	Α
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 8.5 \text{ A}$	-	-	1.2	٧
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 8.5 \text{ A},$	-	313	_	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/ms$	_	4.9	_	μС

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

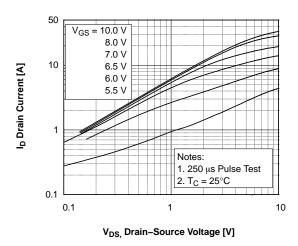


Figure 1. On-Region Characteristics

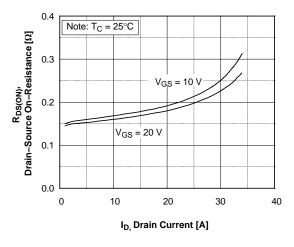


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

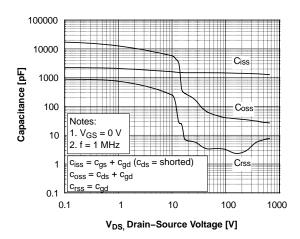


Figure 5. Capacitance Characteristics

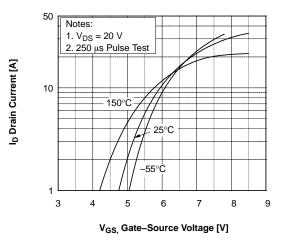


Figure 2. Transfer Characteristics

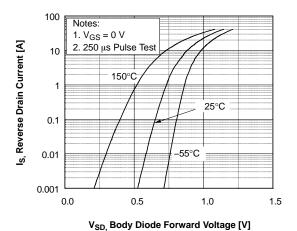


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

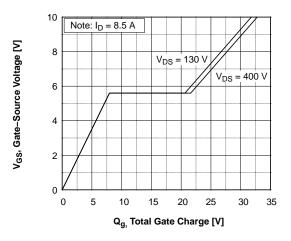


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

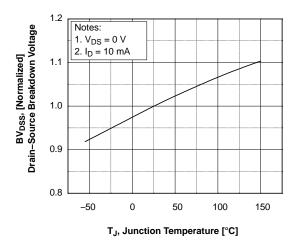


Figure 7. Breakdown Voltage Variation vs. Temperature

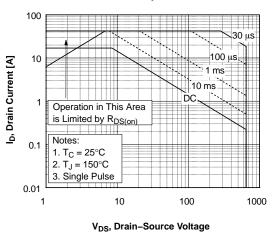


Figure 9. Maximum Safe Operating Area

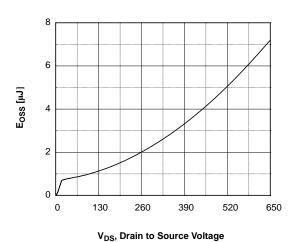
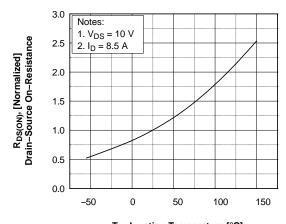


Figure 11. E_{oss} vs. Drain to Source Voltage



T_J, Junction Temperature [°C]

Figure 8. On–Resistance Variation vs.
Temperature

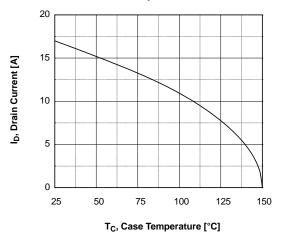


Figure 10. Maximum Drain Current vs.

Case Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

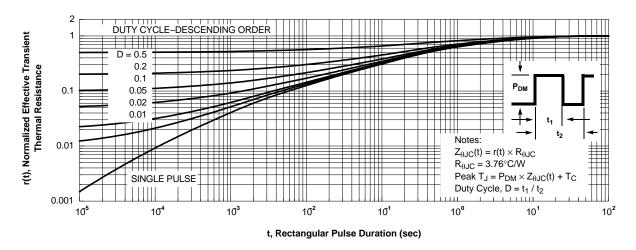


Figure 12. Transient Thermal Response Curve

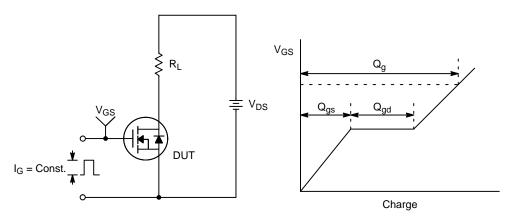


Figure 13. Gate Charge Test Circuit & Waveform

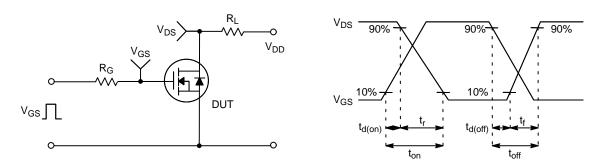


Figure 14. Resistive Switching Test Circuit & Waveforms

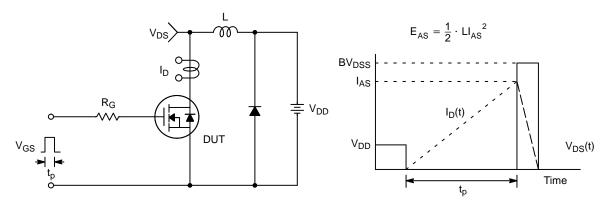


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

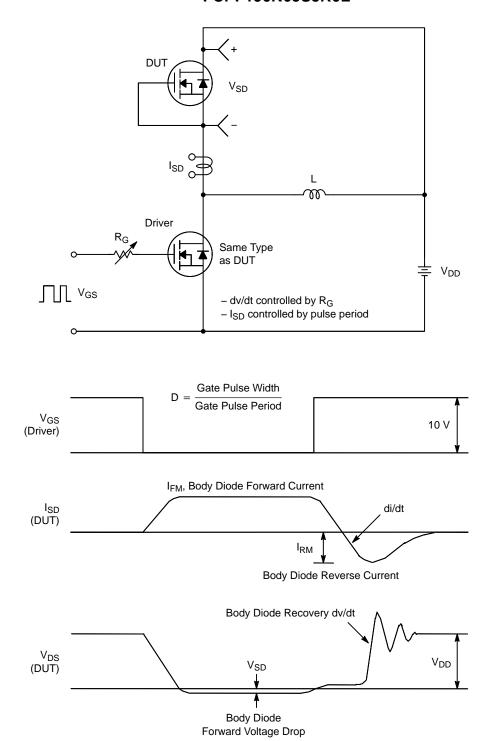
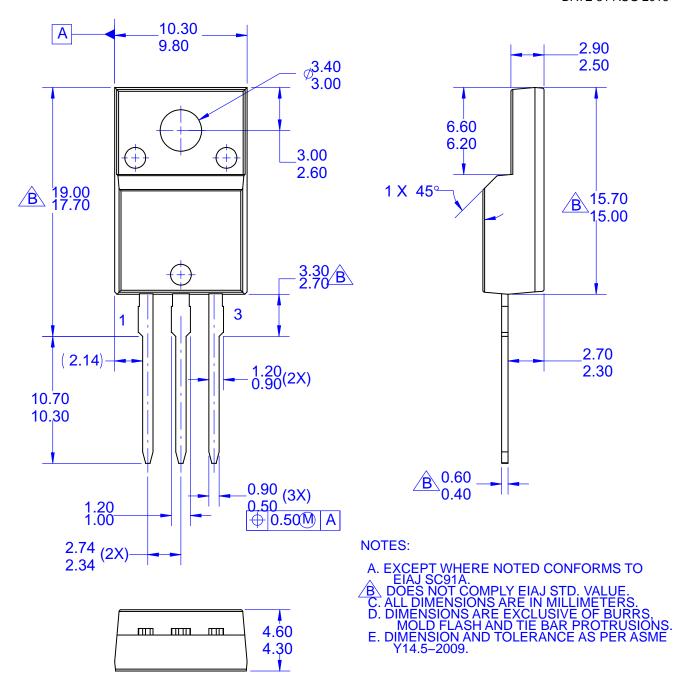


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru_4 moschip.ru_9